

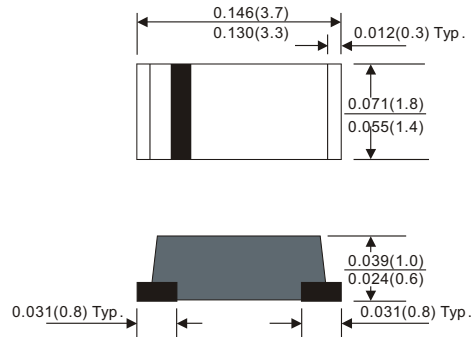
# PSL12-MH thru PSL14-MH

## SILICON EPITAXIAL PLANER TYPE

### Low VF Chip Schottky Diodes



SOD-123H



Dimensions in inches and (millimeters)

### FEATURES

- Plastic package has Underwriters Laboratory
- Flammability Classification 94V-0 Ufizing Flame
- Retardant Epoxy Molding Compound.
- For surface mounted applications.
- Exceeds environmental standards of ML-S-19500/228
- Low leakage current

### MECHANICAL DATA

Case : JEDEC SOD-123H molded plastic  
 Terminals : Solder plated, solderable per  
 MIL-STD-750, Method 2026  
 Polarity : Indicated by cathode band  
 Mounting Position : Any  
 Weight : 0.0393gram

### MAXIMUM RATINGS (at $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	SYMBOL	Min.	Typ.	Max.	UNITS
Forward rectified current	See Fig.2	$I_o$			1.0	A
Forward surge current	8.3ms Single Half Sine-Wave Superimposed on Rated Load (JEDEC Method)	$I_{FSM}$			25	A
Reverse current	$V_R=V_{RRM}$ $T_A=25^\circ\text{C}$	$I_R$			1.0	mA
	$V_R=V_{RRM}$ $T_A=100^\circ\text{C}$				10	mA
Thermal resistance	Junction to ambient	$R_{JA}$		42		$^\circ\text{C} / \text{W}$
Diode junction capacitance	$F=1\text{MHz}$ and applied 4vDC reverse voltage	$C_J$		130		pF
Storage temperature		$T_{STG}$	-55		+150	$^\circ\text{C}$

SYMBOLS	MARKING CODE	$V_{RRM}^{*1}$ (V)	$V_{RMS}^{*2}$ (V)	$V_R^{*3}$ (V)	$V_F^{*4}$ (V)	Operating Temperature ( $^\circ\text{C}$ )
PSL12-MH	L2	20	14	20	0.38	-55 to + 125
PSL13-MH	L3	30	21	30	0.40	
PSL14-MH	L4	40	28	40	0.40	

\*1 Repetitive peak reverse peak reverse

\*2 RMS voltage

\*3 Continuous reverse voltage

\*4 Maximum forward voltage

# PSL12-MH thru PSL14-MH

## SILICON EPITAXIAL PLANER TYPE

### RATING AND CHARACTERISTICS CURVES PSL12-MH THRU PSL14-MH

FIG.1-TYPICAL FORWARD CHARACTERISTICS

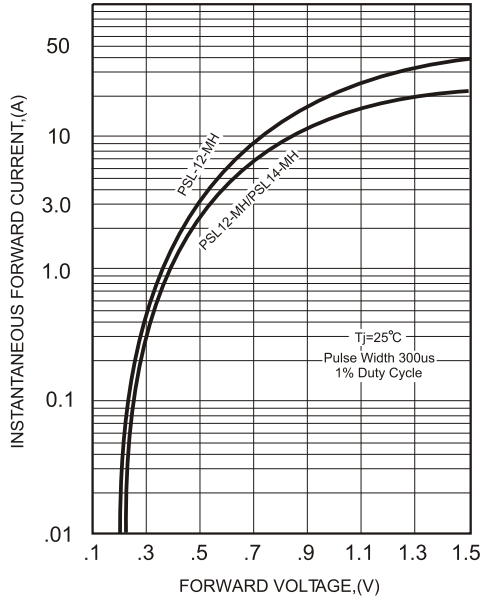


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

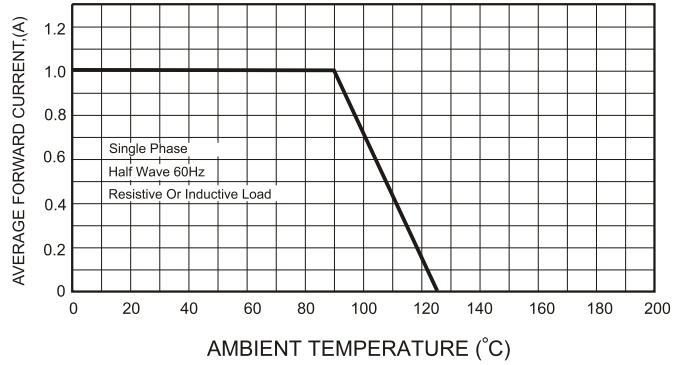


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

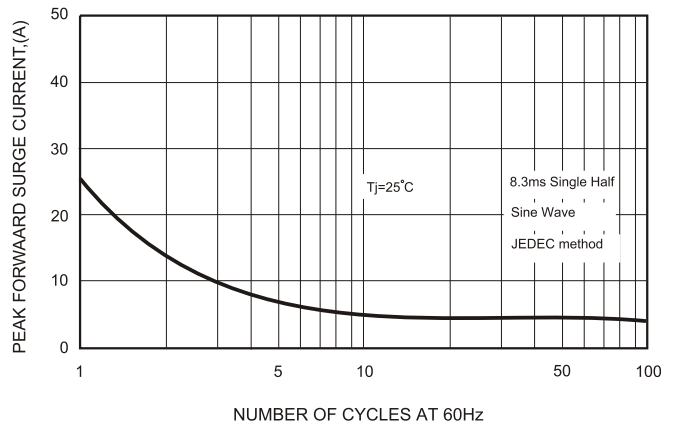


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

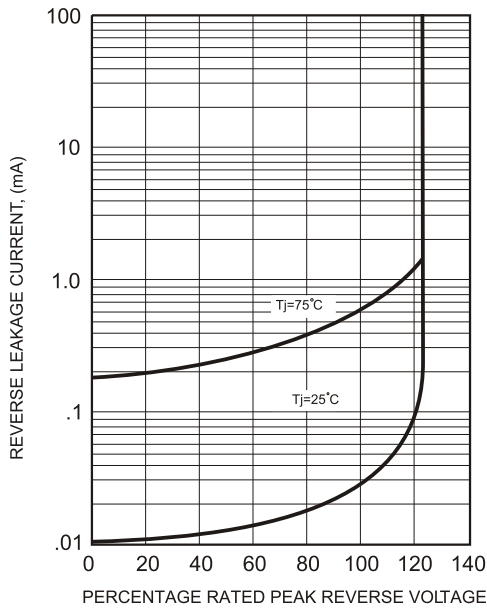


FIG.5-TYPICAL JUNCTION CAPACITANCE

